Unit in mm

TOSHIBA Diode Silicon Epitaxial Planar Type

# HN1D01FU

### Ultra High Speed Switching Application

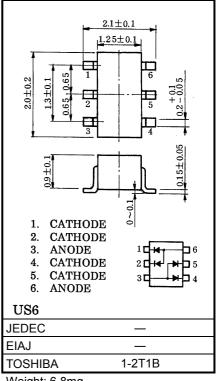
Small package

Low forward voltage  $: V_{F(3)} = 0.92V \text{ (typ.)}$ Fast reverse recovery time:  $t_{rr} = 1.6$ ns (typ.) Small total capacitance  $: C_T = 2.2pF \text{ (typ.)}$ 

### Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit	
Maximum (peak) reverse voltage	$V_{RM}$	85	V	
Reverse voltage	V <sub>R</sub>	80	V	
Maximum (peak) forward current	I <sub>FM</sub>	300*	mA	
Average forward current	Io	100*	mA	
Surge current (10ms)	I <sub>FSM</sub>	2*	Α	
Power dissipation	Р	200	mW	
Junction temperature	Tj	125	°C	
Storage temperature	T <sub>stg</sub>	-55~125	°C	

<sup>\*:</sup> This is the Maximum Ratings of single diode (Q1 or Q2 or Q3 or Q4). In the case of using Unit 1 and Unit 2 independently or simultaneously, the Maximum Ratings per diode is 75% of the single diode one.



Weight: 6.8mg

### Electrical Characteristics (Q1, Q2, Q3, Q4 Common, Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Forward voltage	V <sub>F (1)</sub>	-	I <sub>F</sub> = 1mA	_	0.61	1	V
	V <sub>F (2)</sub>	_	I <sub>F</sub> = 10mA	_	0.74	_	
	V <sub>F (3)</sub>	_	I <sub>F</sub> = 100mA	_	0.92	1.20	
Reverse current	I <sub>R (1)</sub>	_	V <sub>R</sub> = 30V	_	_	0.1	μΑ
	I <sub>R (2)</sub>	_	V <sub>R</sub> = 80V	_	_	0.5	
Total capacitance	C <sub>T</sub>	_	V <sub>R</sub> = 0, f = 1MHz	_	2.2	4.0	pF
Reverse recovery time	t <sub>rr</sub>	_	I <sub>F</sub> = 10mA (fig.1)	_	1.6	4.0	ns

damage to property.

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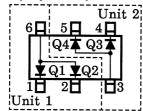
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## Pin Assignment (Top View)



### Marking

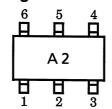
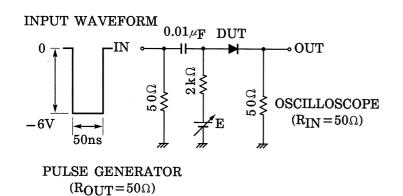
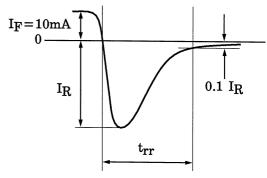


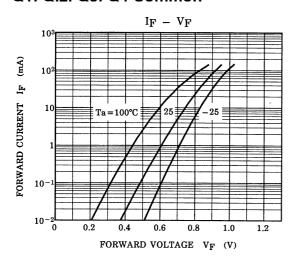
Fig.1 Reverse Recovery Time (trr) Test Circuit



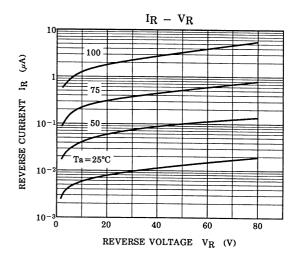




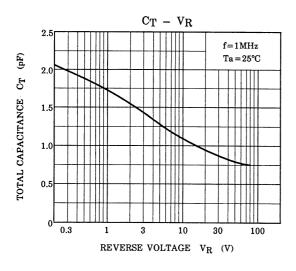
### Q1. Q.2. Q3. Q4 Common



### Q1. Q.2. Q3. Q4 Common



Q1, Q,2, Q3, Q4 Common



Q1, Q,2, Q3, Q4 Common

